

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

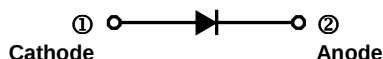
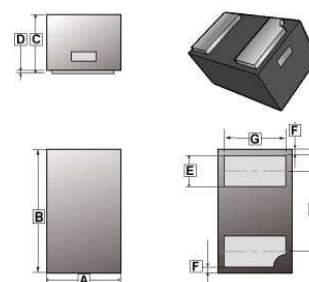
DESCRIPTION

- Silicon epitaxial planar Schottky barrier Diodes
- Small surface mounting type
- High reliability
- Low reverse current and low forward voltage

APPLICATION

- High speed switching For Detection
- For portable equipment:
(i.e. Mobile phone, MP3, MD, CD-ROM,
DVD-ROM, Note book PC, etc.)

DFNWB



PACKAGE INFORMATION

Weight: 0.0123 g (approximately)

MARKING CODE

Cathode - •E +Anode

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.55	0.65	E	0.15	0.35
B	0.95	1.05	F	0.05	REF
C	0.4	0.5	G	0.4	0.6
D	0	0.05	H	0.65	TYP

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (Single diode at $T_A = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
DC Reverse Voltage	V_R	30	V
Mean Rectifying Current	I_O	100	mA
Peak Forward Surge Current	I_{FSM}	500	mA
Junction, Storage Temperature	T_J, T_{STG}	+125, -40 ~ +125	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameters	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward Voltage	V_F	-	-	0.45	V	$I_F = 10\text{mA}$
Reverse Current	I_R	-	-	0.5	μA	$V_R = 10\text{V}$

RATINGS AND CHARACTERISTIC CURVES

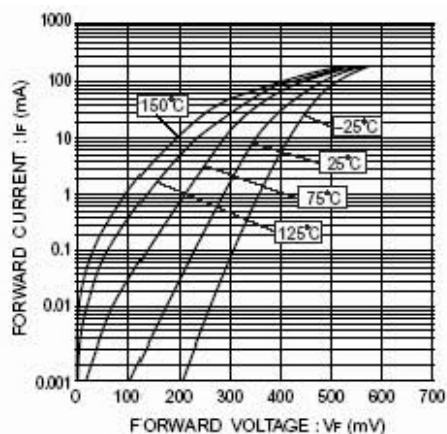


Fig.1 Forward characteristics

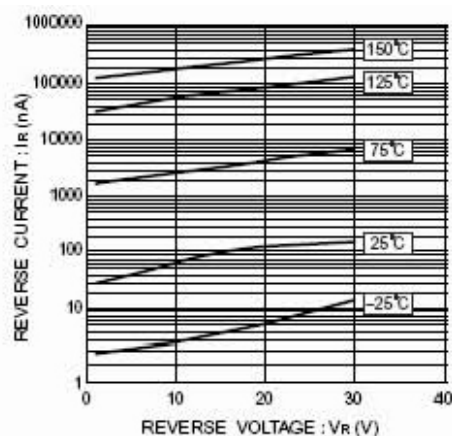


Fig.2 Reverse characteristics

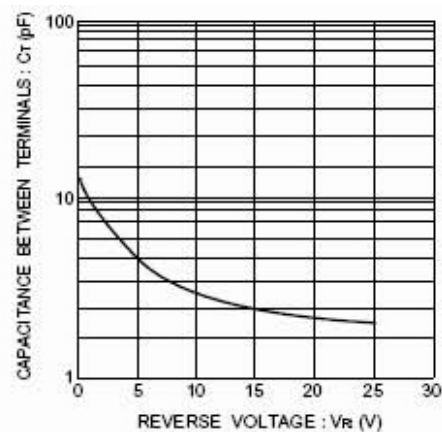


Fig. 3 Capacitance between terminals characteristics